IN THE CLAIMS

Please cancel claim 1 without prejudice or disclaimer and add new claims 37-41 as set forth below.

A3 SUB B1 --37. A semiconductor memory apparatus comprising:

a semiconductor memory device comprising a source region and a drain region, a semiconductor current path connected between the source and the drain regions, a plurality of small memory nodes covered by a potential barrier over the periphery of the memory nodes, a control electrode controlling a voltage of the current path and the memory nodes;

a plurality of the semiconductor memory devices storing an information by a difference of an electron charge in each memory node;

a plurality of control gates connected to each other between the plural semiconductor memory devices; and

wherein a voltage applied between the source and the drain in the semiconductor memory device is different according to the difference in information to be written in a writing operation in the plural semiconductor memory device.

--38. The semiconductor memory device according to claim 37, wherein a large voltage among the voltage applied between

SUB B1

the source and the drain in the semiconductor memory device is over 3 V in the writing operation of the information.

A3 Cont

--39. The semiconductor memory device according to claim 37, wherein a small voltage among the voltage applied between the source and the drain in the semiconductor memory device is substantially 0 V in the writing operation of the information.

--40. The semiconductor memory device according to claim 37, wherein a positive/negative polarity of the voltage applied between the source and the drain in the reading operation for the stored information is opposite from a positive/negative polarity of the voltage applied between the source and the drain in the writing operation.

--41. The semiconductor memory device according to claim 37, wherein the current path is located on the insulator film.--

REMARKS

Claim 1 has been canceled without prejudice or disclaimer. New claims 37-41 have been added. Accordingly, claims 37-41 are currently pending in the application.

The specification and Abstract have been amended as in the parent application. No new matter has been added.